

# **BC817K-40HR Datasheet**



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DiGi Electronics Part Number BC817K-40HR-DG

Manufacturer Nexperia USA Inc.

Manufacturer Product Number BC817K-40HR

Description TRANS NPN 45V 0.5A TO236AB

**Detailed Description** Bipolar (BJT) Transistor NPN 45 V 500 mA 100MHz 3

50 mW Surface Mount TO-236AB



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RFQ Email: Info@DiGi-Electronics.com

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# **Purchase and inquiry**

Manufacturer Product Number:	Manufacturer:
BC817K-40HR	Nexperia USA Inc.
Series:	Product Status:
	Active
Transistor Type:	Current - Collector (Ic) (Max):
NPN	500 mA
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, lc:
45 V	700mV @ 50mA, 500mA
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:
100nA (ICBO)	250 @ 100mA, 1V
Power - Max:	Frequency - Transition:
350 mW	100MHz
Operating Temperature:	Grade:
150°C (TJ)	Automotive
Qualification:	Mounting Type:
AEC-Q101	Surface Mount
Package / Case:	Supplier Device Package:
TO-236-3, SC-59, SOT-23-3	TO-236AB
Base Product Number:	
BC817	

# **Environmental & Export classification**

8541.21.0075

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	



45 V, 500 mA NPN general-purpose transistors
Rev. 1 — 15 December 2017

**Product data sheet** 

## **Product profile**

### 1.1 General description

NPN general-purpose transistors in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

**Table 1. Product overview** 

Type number	Package		PNP complement
	Nexperia	JEDEC	
BC817K-16H	SOT23	TO-236AB	-
BC817K-25H			-
BC817K-40H			-

#### 1.2 Features and benefits

- Three current gain selections
- · High power dissipation capability
- High-temperature applications up to 175 °C
- AEC-Q101 qualified

### 1.3 Applications

General-purpose switching and amplification

### 1.4 Quick reference data

Table 2. Quick reference data

 $T_{amb}$  = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base		-	-	45	V
I <sub>C</sub>	collector current			-	-	500	mA
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-	1	A
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 1 V; I <sub>C</sub> = 100 mA					
	BC817K-16H		[1]	100	-	250	-
	BC817K-25H		[1]	160	-	400	-
	BC817K-40H		[1]	250	-	600	-

[1] pulsed; tp  $\leq$  300  $\mu$ s;  $\delta \leq$  0.02



# 2 Pinning information

Table 3. Pinning

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		
2	Е	emitter	]3	C
3	С	collector	1	BE sym123

# 3 Ordering information

**Table 4. Ordering information** 

Tuble 4. Gracing morning						
Type number	Package					
	Name	Description	Version			
BC817K-16H	TO-236AB	Plastic surface-mounted package; 3 leads	SOT23			
BC817K-25H						
BC817K-40H						

# 4 Marking

Table 5. Marking

Tuble 6. Marking		
Type number		Marking code
BC817K-16H		%HD
BC817K-25H		%HE
BC817K-40H	[1]	%HF

[1] % = placeholder for manufacturing site code

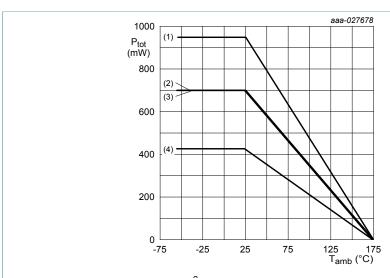
# **Limiting values**

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter	open emitter		50	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	45	V
$V_{EBO}$	emitter-base voltage	open collector		-	7	V
I <sub>C</sub>	collector current			-	500	mA
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms	single pulse; t <sub>p</sub> ≤ 1 ms			Α
I <sub>BM</sub>	peak base current	single pulse; t <sub>p</sub> ≤ 1 ms		-	200	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	425	mW
			[2]	-	700	mW
			[3]	-	700	mW
			[4]	-	950	mW
T <sub>j</sub>	junction temperature			-	175	°C
T <sub>amb</sub>	ambient temperature			-55	175	°C
T <sub>stg</sub>	storage temperature			-65	175	°C

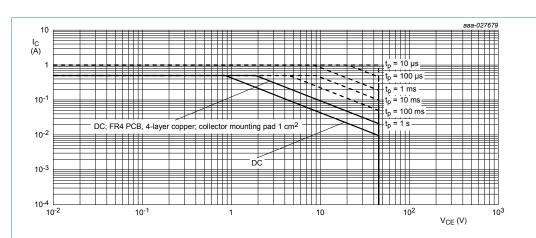
- Device mounted on an FR4 Printed-Circuit-Board (PCB); single-sided copper; tin-plated and standard footprint.
- Device mounted on an FR4 Printed-Circuit-Board (PCB); single-sided copper; tin-plated; mounting pad for collector 1 cm<sup>2</sup>. Device mounted on an FR4 Printed-Circuit-Board (PCB); 4-layer copper; tin-plated and standard footprint. Device mounted on an FR4 Printed-Circuit-Board (PCB); 4-layer copper; tin-plated; mounting pad for collector 1 cm<sup>2</sup>.



- (1) FR4 PCB, 4-layer copper; 1 cm<sup>2</sup>
- (2) FR4 PCB, single-sided copper; 1 cm<sup>2</sup>
- (3) FR4 PCB, 4-layer copper; standard footprint
- (4) FR4 PCB, single-sided copper; standard footprint

Figure 1. Power derating curves

### 45 V, 500 mA NPN general-purpose transistors



FR4 PCB, single-sided copper; standard footprint; single pulse

 $T_{amb}$  = 25 °C

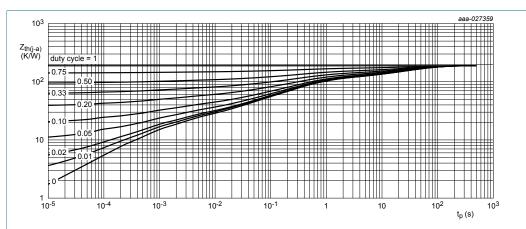
Figure 2. Safe operating area; junction to ambient; continous and peak collector currents as a function of collector-emitter voltage

#### Thermal characteristics

**Table 7. Thermal characteristics** 

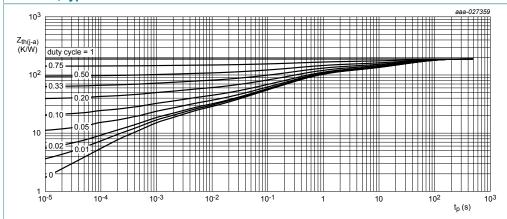
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction	in free air	[1]	-	-	353	K/W
	to ambient		[2]	-	-	215	K/W
			[3]	-	-	215	K/W
			[4]	-	-	158	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	60	K/W

- Device mounted on an FR4 PCB; single-sided copper; tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB; single-sided copper; tin-plated; mounting pad for collector 1 cm<sup>2</sup>.
- Device mounted on an FR4 PCB; 4-layer copper; tin-plated and standard footprint.
- [3] [4] Device mounted on an FR4 PCB; 4-layer copper; tin-plated; mounting pad for collector 1 cm<sup>2</sup>.



FR4 PCB; single-sided copper; tin-plated and standard footprint

Figure 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



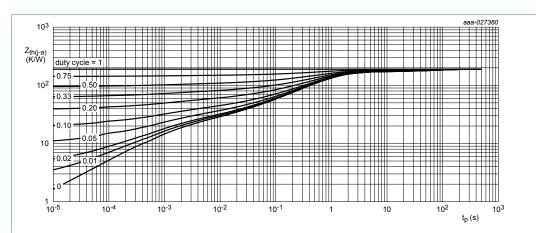
FR4 PCB; single-sided copper; tin-plated; mounting pad for collector 1 cm<sup>2</sup>

Figure 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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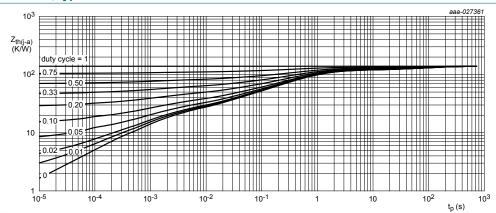
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FR4 PCB; 4-layer copper; tin plated and standard footprint

Figure 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB; 4-layer copper; tin plated; mounting pad for collector 1 cm<sup>2</sup>

Figure 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

45 V, 500 mA NPN general-purpose transistors

### 7 Characteristics

### **Table 8. Characteristics**

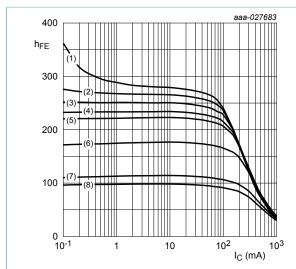
 $T_{amb}$  = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>(BR)CBO</sub>	collector-base breakdown voltage	$I_C = 100 \ \mu A; I_E = 0 \ A$		50	-	-	V
$V_{(BR)CEO}$	collector-emitter breakdown voltage	I <sub>C</sub> = 10 mA; I <sub>B</sub> = 0 A		45	-	-	V
$V_{(BR)EBO}$	emitter-base breakdown voltage	$I_E = 100 \ \mu A; I_C = 0 \ A$		7	-	-	V
I <sub>CBO</sub>	collector-base	V <sub>CB</sub> = 25 V; I <sub>E</sub> = 0 A		-	-	100	nA
	cut-off current	V <sub>CB</sub> = 25 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C		-	-	5	μA
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = 5 V; I <sub>C</sub> = 0 A		-	-	100	nA
h <sub>FE</sub>	DC current gain		'		'	'	
	BC817K-16H	V <sub>CE</sub> = 1 V; I <sub>C</sub> = 100 mA	[1]	100	-	250	
	BC817K-25H	V <sub>CE</sub> = 1 V; I <sub>C</sub> = 100 mA	[1]	160	-	400	
	BC817K-40H	V <sub>CE</sub> = 1 V; I <sub>C</sub> = 100 mA	[1]	250	-	600	
	BC817K-16H, -25H, -40H	V <sub>CE</sub> = 1 V; I <sub>C</sub> = 500 mA	[1]	40	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 500 \text{ mA}; I_B = 50 \text{ mA}$	[1]	-	-	700	mV
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_C = 500 \text{ mA}; I_B = 50 \text{ mA}$	[1]	-	-	1.2	V
V <sub>BE</sub>	base-emitter voltage	V <sub>CE</sub> = 1 V; I <sub>C</sub> = 500 mA	[1]	-	-	1.2	V
f <sub>T</sub>	transition frequency	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 10 mA; f = 100 MHz		100	-	-	MHz
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = 10 V; I <sub>E</sub> = i <sub>e</sub> = 0 A; f = 1 MHz		-	3	-	pF
C <sub>e</sub>	emitter capacitance	$V_{EB} = 0.5 \text{ V}; I_C = I_C = 0 \text{ A}; f = 1 \text{ MHz}$					
	BC817K-16H			-	44	-	pF
	BC817K-25H			-	39	-	pF
	BC817K-40H			-	39	-	pF

<sup>[1]</sup> pulsed;  $t_p \le 300 \ \mu s$ ;  $\delta \le 0.02$ 

# **BC817KH series**

### 45 V, 500 mA NPN general-purpose transistors



 $V_{CE} = 1 V$ 

(1)  $T_{amb}$  = 175 °C

(2) T<sub>amb</sub> = 150 °C

(3)  $T_{amb}$  = 125 °C

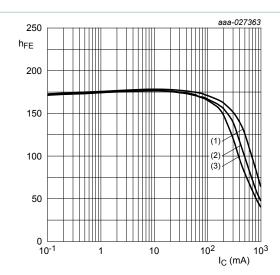
(4)  $T_{amb}$  = 100 °C

(5)  $T_{amb} = 85 \, ^{\circ}C$ 

(6)  $T_{amb}$  = 25 °C

(7)  $T_{amb} = -40 \, ^{\circ}C$ (8)  $T_{amb} = -55 \, ^{\circ}C$ 

Figure 7. BC817K-16H: DC current gain as a function of collector current; typical values



T<sub>amb</sub> = 25 °C

(1)  $V_{CE} = 5 V$ 

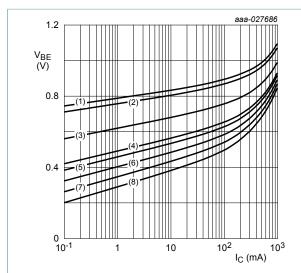
(2)  $V_{CE} = 2 V$ 

(3)  $V_{CE} = 1 V$ 

Figure 8. BC817K-16H: DC current gain as a function of collector current; typical values

# **BC817KH series**

### 45 V, 500 mA NPN general-purpose transistors



 $V_{CE} = 1 V$ 

(1)  $T_{amb} = -55$  °C

(2)  $T_{amb} = -40^{\circ}C$ 

(3)  $T_{amb}$  = 25 °C

(4)  $T_{amb} = 85 \, ^{\circ}C$ 

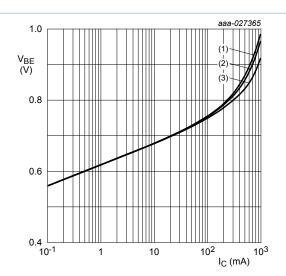
(5)  $T_{amb}$  = 100 °C

(6)  $T_{amb}$  = 125 °C

 $(7) T_{amb} = 150 °C$ 

(8)  $T_{amb} = 175 \, ^{\circ}C$ 

Figure 9. BC817K-16H: Base-emitter voltage as a function of collector current; typical values



 $T_{amb} = 25 \, ^{\circ}C$ 

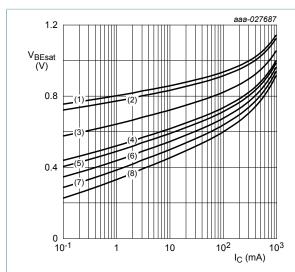
(1)  $V_{CE} = 1 V$ 

(2)  $V_{CE} = 2 V$ 

(3)  $V_{CE} = 5 V$ 

Figure 10. BC817K-16H: Base-emitter voltage as a function of collector current; typical values

45 V, 500 mA NPN general-purpose transistors



 $I_{\rm C}/I_{\rm B} = 10$ 

(1)  $T_{amb} = -55$  °C

(2)  $T_{amb} = -40^{\circ}C$ 

(3)  $T_{amb} = 25 \, ^{\circ}C$ 

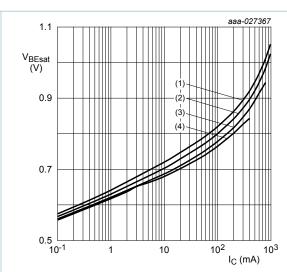
(4)  $T_{amb}$  = 85 °C

 $(5) T_{amb} = 100 °C$ 

(6)  $T_{amb}$  = 125 °C

 $(7) T_{amb} = 150 °C$ 

(8)  $T_{amb} = 175 \, ^{\circ}C$ 



T<sub>amb</sub> = 25 °C

(1)  $I_C/I_B = 10$ 

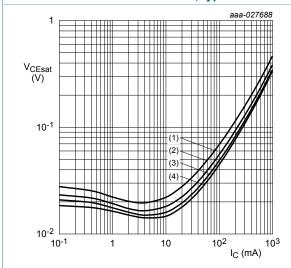
(2)  $I_C/I_B = 20$ 

(3)  $I_C/I_B = 50$ 

 $(4) I_C/I_B = 100$ 

Figure 12. BC817K-16H: Base-emitter saturation voltage as a function of collector current; typical values





 $I_{\rm C}/I_{\rm B}=10$ 

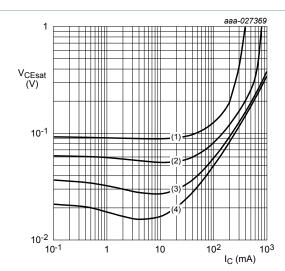
(1)  $T_{amb} = 175 \, ^{\circ}C$ 

(2)  $T_{amb}$  = 85 °C

(3)  $T_{amb} = 25 \, ^{\circ}C$ 

(4)  $T_{amb}$  = -40 °C

Figure 13. BC817K-16H: Collector-emitter saturation voltage as a function of collector current; typical values



 $T_{amb}$  = 25 °C

(1)  $I_C/I_B = 100$ 

(2)  $I_C/I_B = 50$ 

(3)  $I_C/I_B = 20$ 

 $(4) I_C/I_B = 10$ 

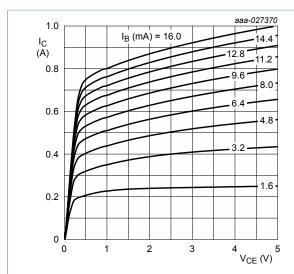
Figure 14. BC817K-16H: Collector-emitter saturation voltage as a function of collector current; typical values

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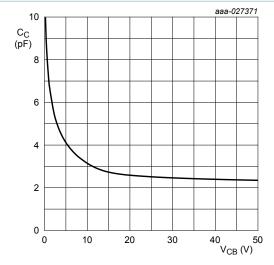
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### 45 V, 500 mA NPN general-purpose transistors



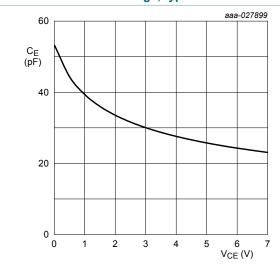
 $T_{amb}$  = 25 °C

Figure 15. BC817K-16H: Collector current as a function of collector-emitter voltage; typical values



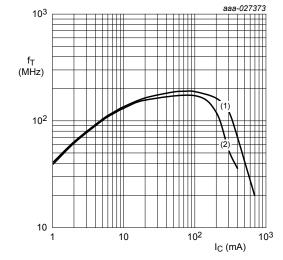
 $f = 1 MHz; T_{amb} = 25 °C$ 

Figure 16. BC817K-16H: Collector capacitance as a function of collector-base voltage; typical values



 $f = 1 MHz; T_{amb} = 25 °C$ 

Figure 17. BC817K-16H: Emitter capacitance as a function of emitter-base voltage; typical values



 $f = 100 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$ 

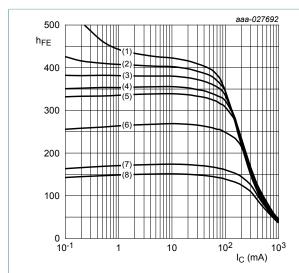
(1)  $V_{CE} = 5 V$ 

(2)  $V_{CE} = 1 V$ 

Figure 18. BC817K-16H: Transition frequency as a function of collector current voltage; typical values

# **BC817KH series**

### 45 V, 500 mA NPN general-purpose transistors



 $V_{CE} = 1 V$ 

(1)  $T_{amb}$  = 175 °C

(2) T<sub>amb</sub> = 150 °C

(3)  $T_{amb}$  = 125 °C

(4)  $T_{amb} = 100 \, ^{\circ}C$ 

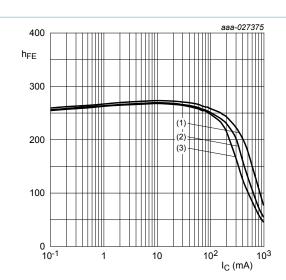
(5)  $T_{amb} = 85 \, ^{\circ}C$ 

(6)  $T_{amb}$  = 25 °C

 $(7) T_{amb} = -40 °C$ 

(8)  $T_{amb} = -55$  °C

Figure 19. BC817K-25H: DC current gain as a function of collector current; typical values



 $T_{amb}$  = 25 °C

(1)  $V_{CE} = 5 V$ 

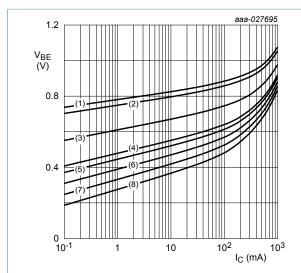
(2)  $V_{CE} = 2 V$ 

(3)  $V_{CE} = 1 V$ 

Figure 20. BC817K-25H: DC current gain as a function of collector current; typical values

# **BC817KH series**

### 45 V, 500 mA NPN general-purpose transistors



 $V_{CE} = 1 V$ 

(1)  $T_{amb} = -55$  °C

(2)  $T_{amb} = -40^{\circ}C$ 

(3)  $T_{amb}$  = 25 °C

(4)  $T_{amb}$  = 85 °C

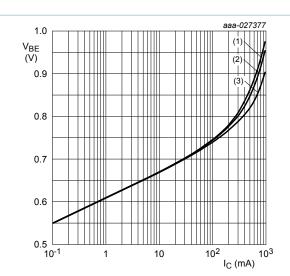
(5)  $T_{amb} = 100 \, ^{\circ}C$ 

(6)  $T_{amb}$  = 125 °C

 $(7) T_{amb} = 150 °C$ 

(8)  $T_{amb}$  = 175 °C

Figure 21. BC817K-25H: Base-emitter voltage as a function of collector current; typical values



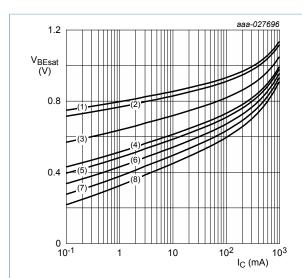
T<sub>amb</sub> = 25 °C

(1)  $V_{CE} = 1 V$ 

(2)  $V_{CE} = 2 V$ 

(3)  $V_{CE} = 5 V$ 

Figure 22. BC817K-25H: Base-emitter voltage as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B} = 10$ 

(1) 
$$T_{amb} = -55$$
 °C

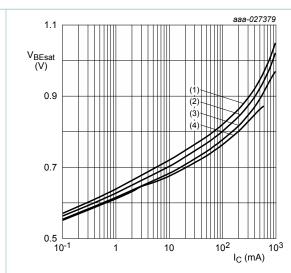
(2) 
$$T_{amb} = -40^{\circ}C$$

(3) 
$$T_{amb} = 25 \, ^{\circ}C$$

$$(5) T_{amb} = 100 °C$$

$$(7) T_{amb} = 150 °C$$

(8)  $T_{amb}$  = 175 °C



T<sub>amb</sub> = 25 °C

(1) 
$$I_C/I_B = 10$$

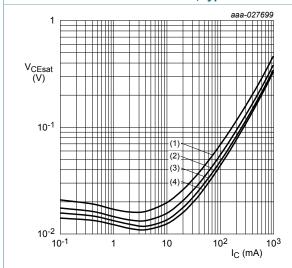
(2) 
$$I_C/I_B = 20$$

(3) 
$$I_C/I_B = 50$$

 $(4) I_C/I_B = 100$ 

Figure 24. BC817K-25H: Base-emitter saturation voltage as a function of collector current; typical values





 $I_{\rm C}/I_{\rm B}=10$ 

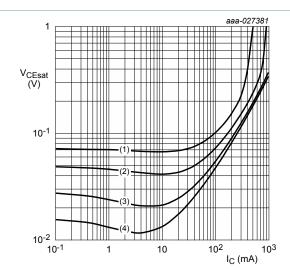
(1) 
$$T_{amb} = 175 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 85 °C

(3) 
$$T_{amb} = 25 \, ^{\circ}C$$

(4) 
$$T_{amb}$$
 = -40 °C

Figure 25. BC817K-25H: Collector-emitter saturation voltage as a function of collector current; typical values



T<sub>amb</sub> = 25 °C

(1) 
$$I_C/I_B = 100$$

(2) 
$$I_C/I_B = 50$$

(3) 
$$I_C/I_B = 20$$

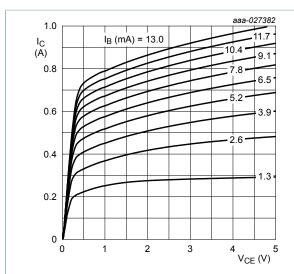
$$(4) I_C/I_B = 10$$

Figure 26. BC817K-25H: Collector-emitter saturation voltage as a function of collector current; typical values

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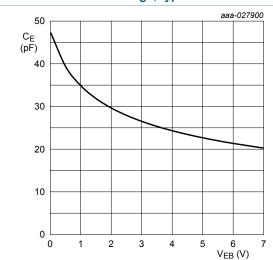
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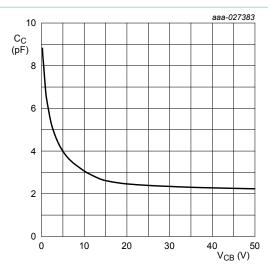
 $T_{amb}$  = 25 °C

Figure 27. BC817K-25H: Collector current as a function of collector-emitter voltage; typical values



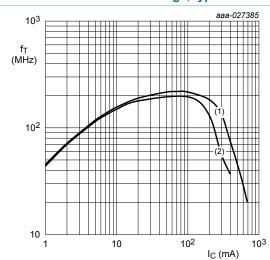
 $f = 1 \text{ MHz}; T_{amb} = 25 \text{ }^{\circ}\text{C}$ 

Figure 29. BC817K-25H: Emitter capacitance as a function of emitter-base voltage; typical values



 $f = 1 MHz; T_{amb} = 25 °C$ 

Figure 28. BC817K-25H: Collector capacitance as a function of collector-base voltage; typical values



 $f = 100 \text{ MHz}; T_{amb} = 25 \text{ }^{\circ}\text{C}$ 

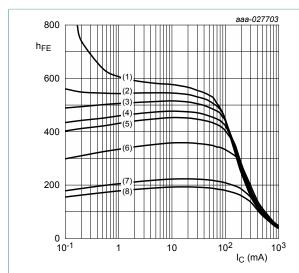
(1)  $V_{CE} = 5 V$ 

(2)  $V_{CE} = 1 V$ 

Figure 30. BC817K-25H: Transition frequency as a function of collector current voltage; typical values

# **BC817KH series**

### 45 V, 500 mA NPN general-purpose transistors



 $V_{CE} = 1 V$ 

(1)  $T_{amb}$  = 175 °C

(2) T<sub>amb</sub> = 150 °C

(3)  $T_{amb}$  = 125 °C

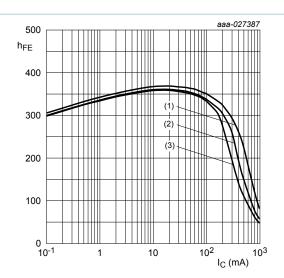
(4)  $T_{amb}$  = 100 °C

(5)  $T_{amb} = 85 \, ^{\circ}C$ 

(6)  $T_{amb}$  = 25 °C

(7)  $T_{amb}$  = -40 °C





 $T_{amb}$  = 25 °C

(1)  $V_{CE} = 5 V$ 

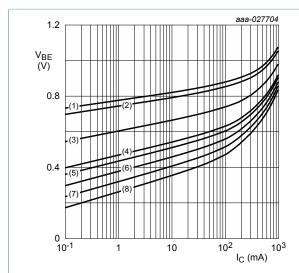
(2)  $V_{CE} = 2 V$ 

(3)  $V_{CE} = 1 V$ 

Figure 32. BC817K-40H: DC current gain as a function of collector current; typical values

# **BC817KH series**

### 45 V, 500 mA NPN general-purpose transistors



 $V_{CE} = 1 V$ 

(1)  $T_{amb} = -55$  °C

(2)  $T_{amb} = -40^{\circ}C$ 

(3)  $T_{amb}$  = 25 °C

(4)  $T_{amb}$  = 85 °C

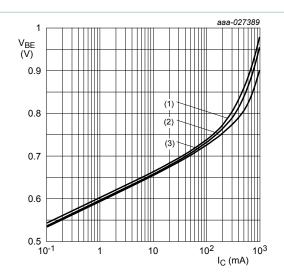
(5)  $T_{amb}$  = 100 °C

(6)  $T_{amb}$  = 125 °C

 $(7) T_{amb} = 150 °C$ 

(8)  $T_{amb}$  = 175 °C

Figure 33. BC817K-40H: Base-emitter voltage as a function of collector current; typical values



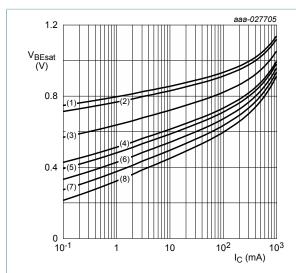
T<sub>amb</sub> = 25 °C

 $(1) V_{CE} = 1 V$ 

(2)  $V_{CE} = 2 V$ 

 $(3) V_{CE} = 5 V$ 

Figure 34. BC817K-40H: Base-emitter voltage as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B} = 10$ 

(1)  $T_{amb} = -55$  °C

(2)  $T_{amb} = -40^{\circ}C$ 

(3)  $T_{amb} = 25 \, ^{\circ}C$ 

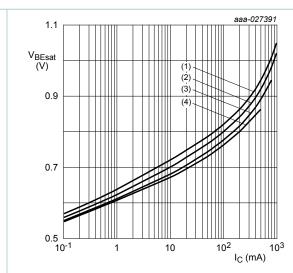
(4)  $T_{amb}$  = 85 °C

(5)  $T_{amb} = 100 \, ^{\circ}C$ 

(6)  $T_{amb} = 125 \, ^{\circ}C$ 

 $(7) T_{amb} = 150 °C$ 

(8)  $T_{amb} = 175 \, ^{\circ}C$ 



T<sub>amb</sub> = 25 °C

(1)  $I_C/I_B = 10$ 

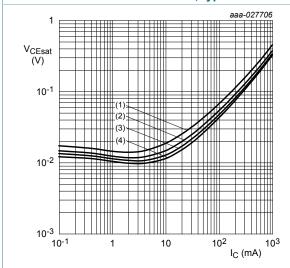
(2)  $I_C/I_B = 20$ 

(3)  $I_C/I_B = 50$ 

 $(4) I_C/I_B = 100$ 

Figure 36. BC817K-40H: Base-emitter saturation voltage as a function of collector current; typical values





 $I_{\rm C}/I_{\rm B}=10$ 

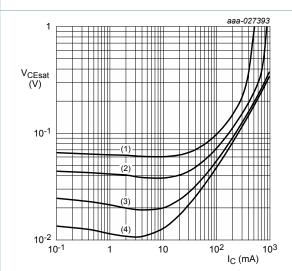
(1)  $T_{amb} = 175 \, ^{\circ}C$ 

(2)  $T_{amb}$  = 85 °C

(3)  $T_{amb} = 25 \, ^{\circ}C$ 

(4)  $T_{amb}$  = -40 °C

Figure 37. BC817K-40H: Collector-emitter saturation voltage as a function of collector current; typical values



 $T_{amb} = 25 \, ^{\circ}C$ 

(1)  $I_C/I_B = 100$ 

(2)  $I_C/I_B = 50$ 

(3)  $I_C/I_B = 20$ 

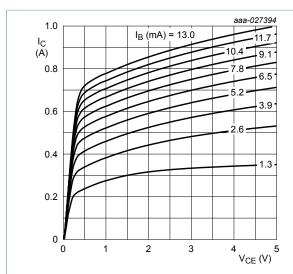
 $(4) I_C/I_B = 10$ 

Figure 38. BC817K-40H: Collector-emitter saturation voltage as a function of collector current; typical values

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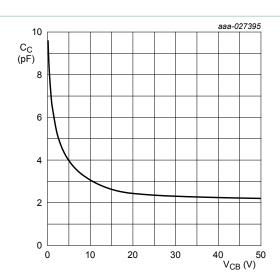
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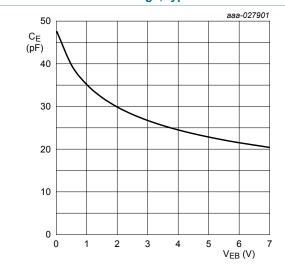
 $T_{amb}$  = 25 °C

Figure 39. BC817K-40H: Collector current as a function of collector-emitter voltage; typical values



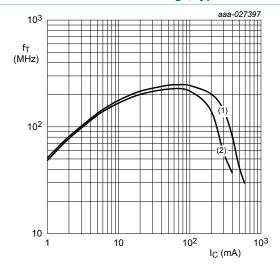
f = 1 MHz; T<sub>amb</sub> = 25 °C

Figure 40. BC817K-40H: Collector capacitance as a function of collector-base voltage; typical values



f = 1 MHz;  $T_{amb} = 25 \text{ °C}$ 

Figure 41. BC817K-40H: Emitter capacitance as a function of emitter-base voltage; typical values



f = 100 MHz;  $T_{amb} = 25 \text{ °C}$ 

(1)  $V_{CE} = 5 V$ 

(2)  $V_{CE} = 1 V$ 

Figure 42. BC817K-40H: Transition frequency as a function of collector current voltage; typical values

### 8 Test information

### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

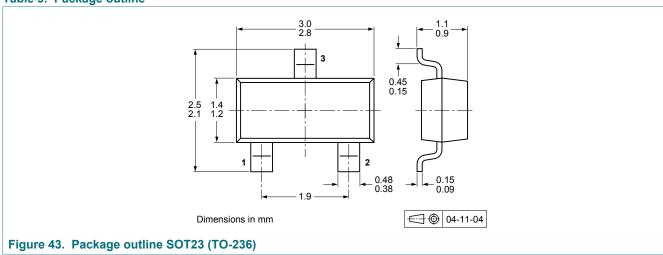
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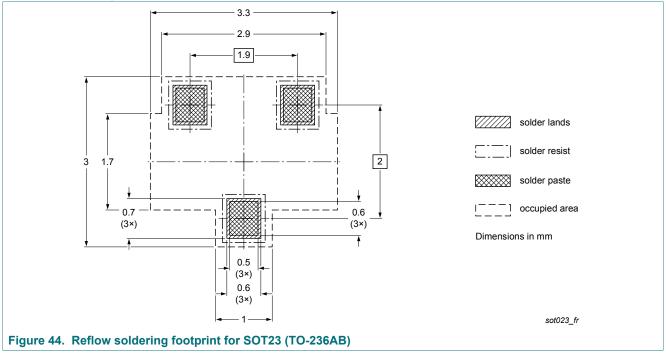
# 9 Package outline

#### Table 9. Package outline

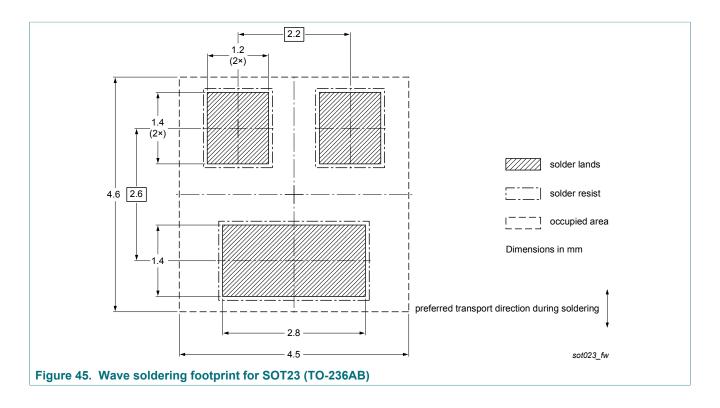


# 10 Soldering

#### Table 10. Soldering



### 45 V, 500 mA NPN general-purpose transistors



# **BC817KH** series

45 V, 500 mA NPN general-purpose transistors

# 11 Revision history

#### Table 11. Revision history

Document ID		Data sheet status	Change notice	Supersedes
BC817KH_SER v.1	20171215	Product data sheet	-	-

# 12 Legal information

#### 12.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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# **BC817KH series**

### 45 V, 500 mA NPN general-purpose transistors

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# **BC817KH series**

45 V, 500 mA NPN general-purpose transistors

### **Contents**

1	Product profile	1
1.1	General description	
1.2	Features and benefits	
1.3	Applications	1
1.4	Quick reference data	1
2	Pinning information	2
3	Ordering information	2
4	Marking	
5	Limiting values	3
6	Thermal characteristics	
7	Characteristics	7
8	Test information	19
8.1	Quality information	19
9	Package outline	20
10	Soldering	
11	Revision history	
12	Legal information	

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